

SMD Schottky Barrier Diode

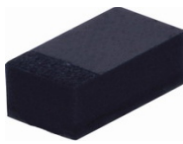


SMD Diodes Specialist

CDBFR0140L (RoHs Device)

$I_o = 100\text{ mA}$

$V_R = 40\text{ Volts}$

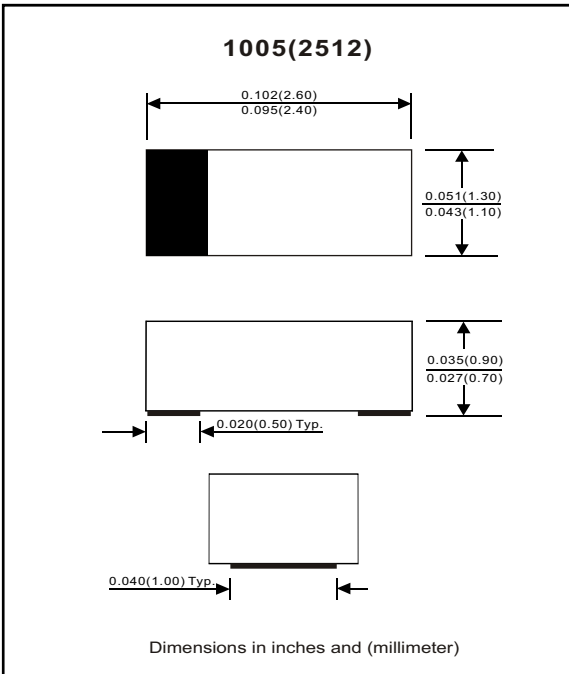


Features

- Low forward voltage.
- Designed for mounting on small surface.
- Extremely thin / leadless package.
- Majority carrier conduction.

Mechanical data

- Case: 1005(2512) standard package, Molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750,method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any
- Weight: 0.006 gram(approx.).



Maximum Rating (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive Peak reverse voltage		V_{RRM}			45	V
Reverse voltage		V_R			40	V
Average forward rectified current		I_o			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}			1	A
Storage temperature		T_{STG}	-40		+125	$^{\circ}\text{C}$
Junction temperature		T_j			+125	$^{\circ}\text{C}$

Electrical Characteristics (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100\text{mA}$ $I_F = 10\text{mA}$	V_F			0.55 0.34	V
Reverse current	$V_R = 10\text{V}$	I_R			30	μA
Capacitance between terminals	$f = 1\text{ MHz}$, and 10 VDC reverse voltage	C_T		6		pF

RATING AND CHARACTERISTIC CURVES (CDBFR0140L)

Fig. 1 - Forward characteristics

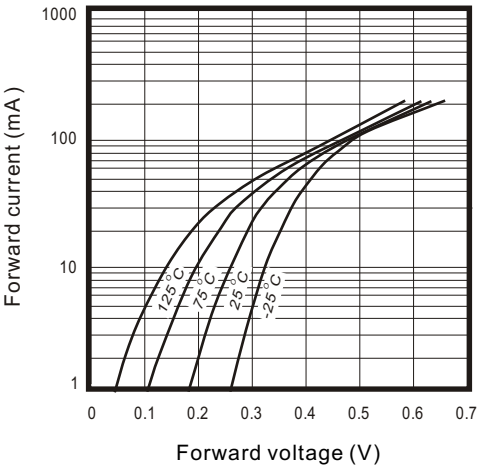


Fig. 2 - Reverse characteristics

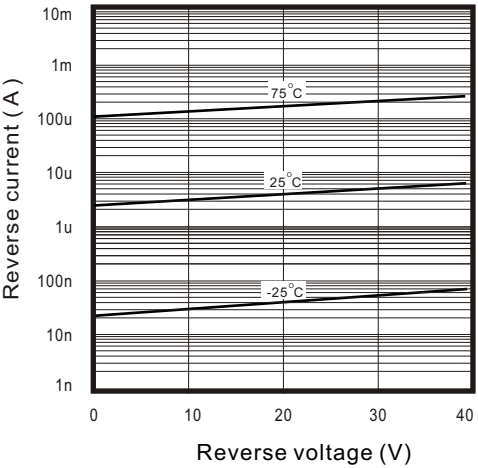


Fig. 3 - Capacitance between terminals characteristics

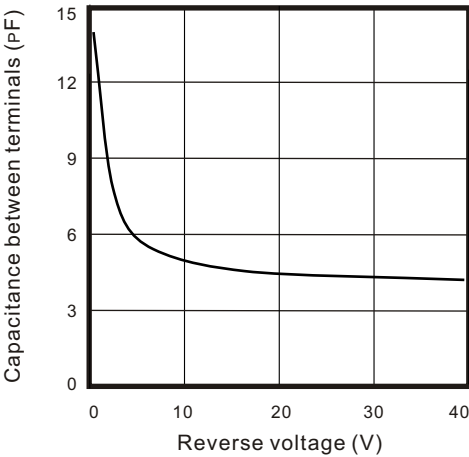


Fig.4 - Current derating curve

